

[Name of Document] Abstract

DIE-BONDING LAYER FORMATION FILM, PROCESSED PRODUCT HAVING
DIE-BONDING LAYER FORMATION FILM ATTACHED THERETO, AND
5 SEMICONDUCTOR DEVICE

A die-bonding layer formation film (1) to be used for
fixing a processed product to an adherend, the processed product
being obtained by processing a workpiece, the die-bonding layer
10 formation film (1) comprising an adhesive layer, wherein, when
a temperature dependency of a storage elastic modulus of the
adhesive layer is measured, the storage elastic modulus has a
local minimum value at a temperature within a range of 80°C to
150°C, wherein the adhesive layer has a shear strength to a
15 peeling strength test substrate of 20 N/2 mm² or more and 50
N/2 mm² or less, wherein the shear strength is measured after
the processed product is placed above the peeling strength test
substrate via the die-bonding layer formation film (1) and the
die-bonding layer formation film (1) on the peeling strength
20 test substrate is heated at 175°C for 1 hour and then further
maintained under an environment of 250°C for 30 seconds.
According to the die-bonding layer formation film (1), bubbles
(voids) are unlikely to grow at the boundary between the
adhesive layer and an adherend even when subjected to thermal
25 history, and the adhesive layer is excellent in the suitability
for wire bonding.

Fig. 1